

March 2015

MTD3055VL

N-Channel Logic Level Enhancement Mode Field Effect Transistor

General Description

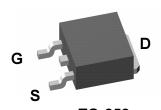
This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $\rm R_{\rm DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

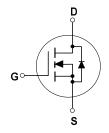
Features

- 12 A, 60 V. $R_{DS(ON)} = 0.18 \Omega @ V_{GS} = 5 V$
- Critical DC electrical parameters specified at elevated temperature.
- Low drive requirements allowing operation directly from logic drivers. Vgs(th) < 2 V.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.



TO-252

Absolute Maximum Ratings Tc=25°C unless otherwise noted



Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	60	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Maximum Drain Current -Continuous (Note 1)	12	А
	T _C = 100°C (Note 1)	8	1
	Maximum Drain Current -Pulsed	42	1
P _D	Maximum Power Dissipation @ $T_c = 25^{\circ}C$ (Note 1)	48	W
	$T_A = 25^{\circ}C$ (Note 1a)	3.9	1
	$T_A = 25$ °C (Note 1b)	1.5	1
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +175	∘c

Thermal Characteristics R. D. Thermal Resistance, Junction-to- Case (Note 1)

R _{eJC}	Thermal Resistance, Junction-to- Case	(Note 1)	3.13	∘C/W
R _{eJA}	Thermal Resistance, Junction-to- Ambient	(Note 1a)	71.4	∘C/W
•				

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
MTD3055VL	MTD3055VL	13"	16mm	2500

^{*} Die and manufacturing source subject to change without prior notification.

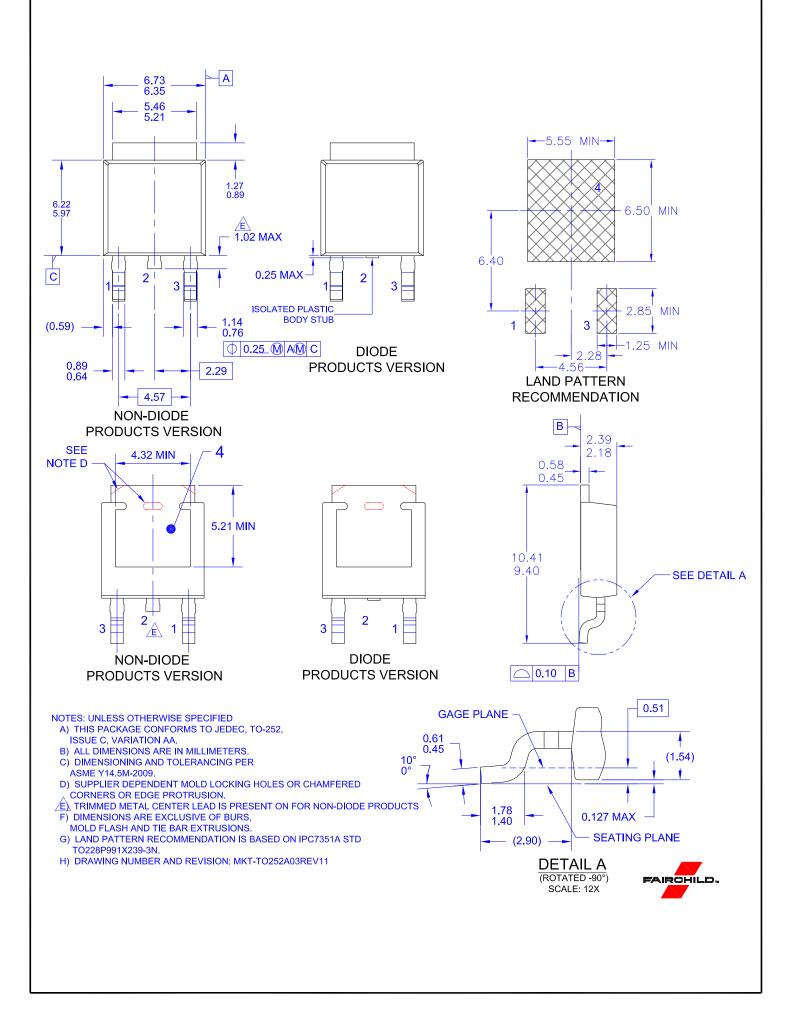
©1999 Fairchild Semiconductor Corporation MTD3055VL Rev. 1.1

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RATI	NGS (Note 2)				!
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	V _{DD} = 25 V, I _D = 12 A			72	mJ
I _{AR}	Maximum Drain-Source Avalanche	Current			12	Α
Off Chara	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	60			V
$\frac{\Delta BV_DSS}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 _μ A, Referenced to 25∘C		54		mV/∘C
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V			10	μΑ
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 150∘C			100	
GSSF	Gate-Body Leakage Current, Forward	V _{GS} = 15 V, V _{DS} = 0 V			100	nA
GSSR	Gate-Body Leakage Current, Reverse	$V_{GS} = -15 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Chara	acteristics (Note 2)					
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.5	2	V
$\frac{\Delta V^{\text{GS(th)}}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-2.6		mV/∘C
R _{DS(on)}	Static Drain-Source On-Resistance	$V_{GS} = 5 V, I_{D} = 6 A,$			0.18	Ω
$V_{DS(on)}$	Drain-Source On-Voltage On-Resistance	V _{GS} = 5 V, I _D = 12 A I _D = 6 A, T _J =150∘C			2.6 2.5	V
g _{FS}	Forward Transconductance	V _{DS} = 8 V, I _D = 6 A	5.0			S
<u>Dynamic</u>	Characteristics				-	
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$			570	pF
C_{oss}	Output Capacitance	f = 1.0 MHz			160	pF
C _{rss}	Reverse Transfer Capacitance				40	pF
Switching	g Characteristics (Note 2)				•	•
t _{d(on)}	Turn-On Delay Time	V _{DD} = 30 V, I _D = 12 A,			20	ns
tr	Turn-On Rise Time	$V_{GS} = 5 \text{ V}, R_{GEN} = 9.1 \Omega$			190	ns
t _{d(off)}	Turn-Off Delay Time				30	ns
t _f	Turn-Off Fall Time				90	ns
Q _g	Total Gate Charge	V _{DS} = 48 V,			10	nC
Q_{gs}	Gate-Source Charge	I _D = 12 A, V _{GS} = 5 V		2		nC
Q _{gd}	Gate-Drain Charge			6.1		nC
	urce Diode Characteristics	and Maximum Ratings	•		•	•
Is	Maximum Continuous Drain-Sourc				12	Α
I _{SM}	Maximum Pulsed Drain-Source Did	ode Forward Current (Note 2)			42	А
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \ V_1 _{S} = 12 \ A$ (Note 2)			1.3	٧
t _{rr}	Drain-Source Reverse Recovery Time	l _F = 12 A, di/dt = 100A/μs		51		nS

[.] $R_{\rm BJA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance whe $R_{\rm BJC}$ is guaranteed by design while $R_{\rm BCA}$ is determined by the user's board design.



Scale 1 : 1 on letter size paper 2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%







TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ F-PFS™ AttitudeEngine™ FRFET®

Global Power ResourceSM Awinda[®] AX-CAP®*

GreenBridge™ BitSiC™ Green FPS™ Build it Now™ Green FPS™ e-Series™

CorePLUS™ Gmax™ CorePOWER™ $\mathsf{GTO}^{\mathsf{TM}}$ CROSSVOLT™ IntelliMAX™ CTL™ ISOPLANAR™

Current Transfer Logic™ Making Small Speakers Sound Louder

DEUXPEED® and Better™ Dual Cool™ MegaBuck™ EcoSPARK® MIČROCOUPLER™ EfficientMax™ MicroFET™

MicroPak™ MicroPak2™ MillerDrive™ MotionMax™ Fairchild Semiconductor® MotionGrid® FACT Quiet Series™

MTi[®] FACT[®] MTx® FastvCore™ MVN® FETBench™ mWSaver® FPS™ OptoHiT™ OPTOLOGIC® OPTOPLANAR®

Power Supply WebDesigner™ PowerTrench®

PowerXSTI

Programmable Active Droop™

OFFT QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

SPM® STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™ Sync-Lock™

SYSTEM SYSTEM

TinyBoost[®] TinyBuck[®] TinyCalc™ TinyLogic[®] TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TranSiC™

TriFault Detect™ TRUECURRENT®* սSerDes™

UHC Ultra FRFET™ UniFET™ VCX™ VisualMax™

VoltagePlus™ XSTM. Xsens™ 仙童®

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

ESBC™

-®

Fairchild®

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR <u>AIRCHILDSEMI.COM.</u> FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application - including life critical medical equipment - where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com,

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Definition of Terms				
Datasheet Identification	Product Status	Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

Rev 177

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3 2SK2614(TE16L1,Q)